

Double quantum dots as a high sensitive submillimeter-wave detector

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A single electron transistor (SET) consisting of parallel double quantum dots fabricated in a GaAs/Al_xGa_{1-x}As heterostructure crystal is demonstrated to serve as an extremely high sensitive detector of submillimeter waves (SMMW). One of the double dots is ionized by SMMW via Kohn-mode plasma excitation, which affects the SET conductance through the other quantum dot yielding the photoresponse. Noise equivalent power of the detector for wavelengths about 0.6 mm is estimated to reach the order of 10^{-17} W/ $\sqrt{Hz}$ at 70 mK.

Single-photon detection (SPD) has been achieved in the far-infrared range by exploiting cyclotron-resonance in a semiconductor quantum dot (QD) in high magnetic fields [1–3]. From the viewpoint of wide application as a detector, it is of great importance to realize SPD without magnetic fields as well as to expand the wavelength range. We demonstrate here that a double QD operated as a single electron transistor (SET) provides a novel mechanism of detecting submillimeter waves (SMMW) with an extremely high sensitivity close to the SPD level in the absence of magnetic fields. The noise equivalent power (NEP) of the detector is estimated to reach the order of 10^{-17} W/ $\sqrt{Hz}$ for the wavelengths of $\lambda = 0.6$ mm, which well exceeds reported characteristics of conventional detectors in the relevant λ -range [4].

The mechanism is described by Figs.1 (a)-(c). The device structure shown on Fig.1(a) is reminiscent of a lateral double-QD SET studied earlier at different groups [5,6]. Adjacent to the first QD (D1) that forms SET, the second QD (D2) is placed and capacitively coupled to D1. D2 is coupled to incident SMMW by a planar dipole antenna. As depicted in Fig.1 (b), if an electron in D2 gains an excess energy E^* through the excitation by SMMW, the excited electron escapes either to D1 or to the electron reservoir adjacent to D2 so that the number of electrons, N_2 , in D2 decreases by one ($\Delta N_2 = -1$). The electron then rapidly releases its excess energy (via phonon emission or electron-electron interaction) relaxing to the Fermi level, ε_F . The potential barriers, in turn, prevent the "cold" electron from returning to D2, thereby realizing a relatively long lifetime τ_l of the ionized state of D2. Letting C_{12} be an inter-QD capacitance and C_i ($i=1$ and

2) capacitances between D_i and the environments, the ionization of D2 ($\Delta N_2 = -1$) decreases the electrochemical potential of D1, μ_1 , by $-\Delta\mu_1 \approx -e^2 C_{12}/C_1 C_2$ (e is the unit charge), where $C_{12} \ll C_1$ and $C_{12} \ll C_2$ hold in the experimental condition. This will result in the shift of SET conductance peak by $-\Delta\mu_1/\varepsilon_{ch} \approx -C_{12}/C_2 = -(3 \sim 15 \%)$ in the sweep of V_{G1} , yielding a detectable conductance change as shown in Fig.1(c), where $\varepsilon_{ch} = e^2/C_1$ is the charging energy of D1 that determines the period of the Coulomb conductance oscillations.

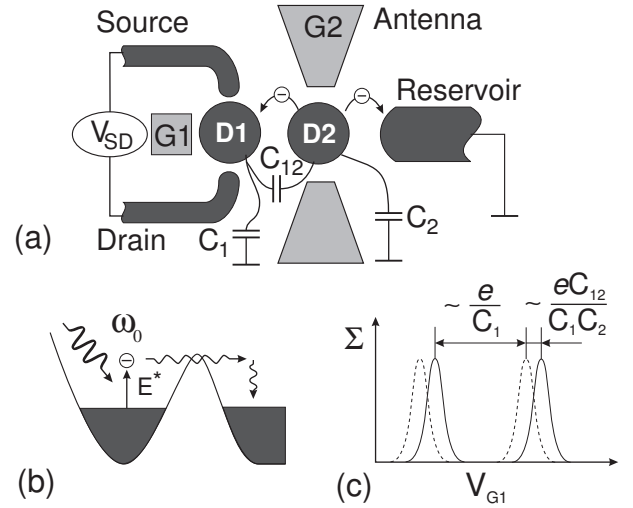


FIG. 1. Schematic representations of the SMMW photon detection. (a) An SET consisting of parallel double QDs. (b) Ionization of D2. (c) Conductance peak shift induced by the ionization.

The inset of Fig.2 schematically shows the device fabricated through a standard lithographic technique on a GaAs/Al_xGa_{1-x}As heterostructure crystal with a mobility of 80 m²/Vs and a sheet carrier density of $n_s = 2.6 \times 10^{15}$ m⁻² at 4.2K. Light areas indicate metal gates deposited on top of the crystal. Negatively biasing the gates depletes the two-dimensional electron gas (2DEG) below the gates and forms D1, D2, the source (S), the drain (D) and the reservoir (R). The lithographic size of each QD is $0.5 \times 0.5 \mu\text{m}^2$, with about 200 electrons in it. The gate B12 defines the inter-QD potential barrier. The control gate, G2, controls not only the electrochemical potential of D2, μ_2 , but also defines the potential barrier between D2 and R. Metal leads for G2 and B12 extend over 0.1 mm in length, forming a dipole antenna for D2. The experiments are performed at 70mK by using a ³He–⁴He dilution refrigerator.

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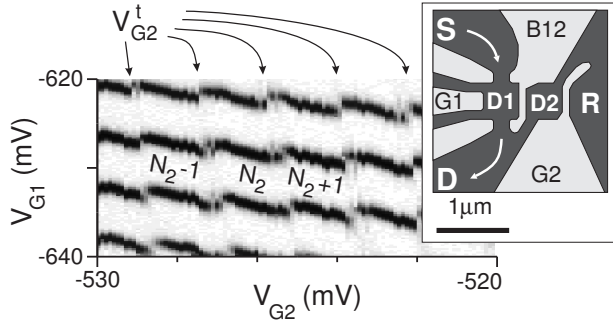


FIG. 2. Conductance peak traces on the plane of V_{G1} and V_{G2} . The device studied is shown in the inset.

The dark regions in Fig. 2 display conductance peak traces without SMMW as a function of the bias voltages V_{G1} and V_{G2} for G1 and G2, with a fixed bias voltage for B12 at $V_{B12} = -532$ mV. As V_{G1} increases, the conductance resonance periodically occurs at the positions where $\mu_1 = \varepsilon_F$, forming a set of dark traces with a spacing proportional to $\varepsilon_{ch} = e^2/C_1$. As V_{G2} increases, each trace shows step-wise small jump in the positive V_{G1} -direction at each transition point V_{G2}^t where N_2 increases by one ($\mu_2 = \varepsilon_F$) [5]. This is because the change $\Delta N_2 = +1$ causes abrupt shift of μ_1 by $+\Delta\mu_1/\varepsilon_{ch} \approx +C_{12}/C_2 \approx 10\%$ at $V_{G2} = V_{G2}^t$.

As a source of SMMW, we use an n-InSb Hall device for most of the studies and a high-mobility GaAs 2DEG Hall bar for spectroscopic measurements, both of which emit relatively narrow cyclotron radiation. The frequency $\omega_c = eB_e/m^*$ (m^* is the effective electron mass) is tunable by scanning the magnetic field B_e for the emitters [3]. To guide the SMMW from the emitters to the sample we use an optical scheme similar to that previously described [3]. The SMMW power, W , incident on the effective antenna area for D2 (about 0.2 mm diameter) is weak, being roughly estimated to be $W \approx 1$ fW or 3×10^6 photons per second in a band width of 0.6 ± 0.2 mm when the electrical input power of $P_{in} = 1$ mW is fed to the n-InSb emitter. The SET conductance is measured with an ac-voltage (25 mV and 1 kHz) while SMMW are applied in a square waveform at a lower frequency (7 Hz). We represent the photoresponse by the difference between the dark conductance Σ_0 and the conductance Σ with SMMW, $\Delta\Sigma \equiv \Sigma - \Sigma_0$, and study it via a double lock-in technique [3]. The wavelength of applied SMMW is in a range 0.6 ± 0.2 mm unless otherwise specified.

Fig. 3 (a) shows a typical photoresponse signal, $\Delta\Sigma$, along with Σ_0 in a sweep of V_{G1} , where $V_{B12} = -532$ mV, $W = 0.3$ fW, and the effective time-constant of the measurements of 1 second. V_{G2} is chosen to be -628 mV, which is close to but higher than a nearest V_{G2}^t . In this gate bias condition, the inter-QD coupling (C_{12}/C_2) is smaller than that for Fig.2. It follows that the step amplitude in the conductance peak traces Σ_0 at each V_{G2}^t ($\Delta N_2 = +1$) is found to be smaller than that seen in Fig.2; viz., $+\Delta\mu_1/\varepsilon_{ch} \approx +C_{12}/C_2 \approx 3 \sim 5\%$.

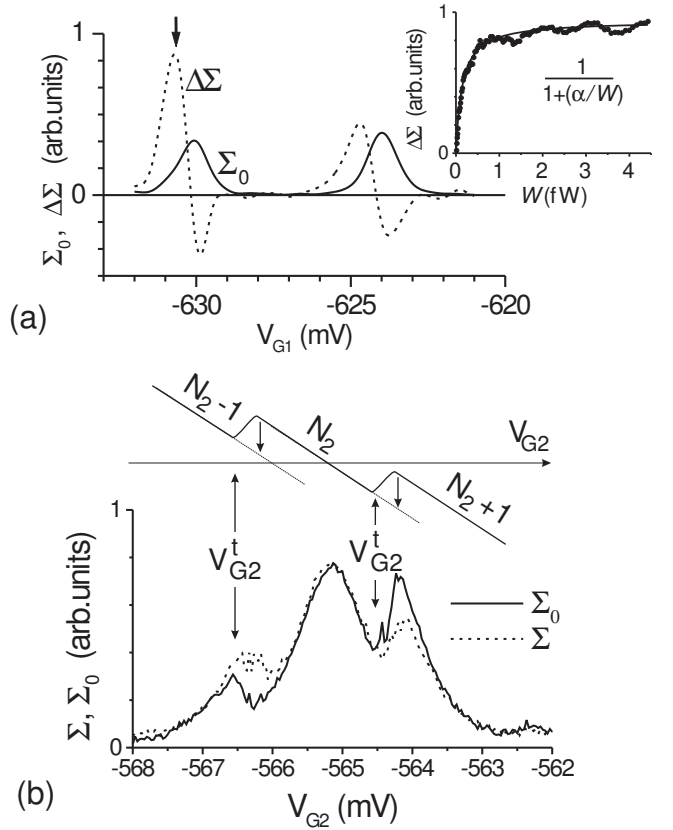


FIG. 3. (a) Conductance peaks, Σ_0 , without SMMW (a solid line) and the photoresponse, $\Delta\Sigma \equiv \Sigma - \Sigma_0$ (a dotted line), as a function of V_{G1} , studied with $W = 0.3$ fW and V_{G2} fixed at -628 mV. The inset shows the amplitude of $\Delta\Sigma$ at the V_{G1} -position marked by the arrow against the radiation intensity. (b) The dark conductance, Σ_0 (a solid line), and the conductance, Σ , under SMMW illumination (a dotted line: $W = 2$ fW), as a function of V_{G2} with V_{G1} fixed at -630 mV. A solid line with steps in the upper space schematically represents the conductance peak trace, while the horizontal straight line indicates the trace along which V_{G2} is scanned.

The curve of $\Delta\Sigma$ versus V_{G1} shows that the SMMW causes the conductance peak to shift towards the negative direction of V_{G1} by $3 \sim 5\%$, strongly suggesting the ionization of D2 ($\Delta N_2 = -1$). Though not shown here, we have carefully confirmed that the shape of the $\Delta\Sigma$ versus V_{G1} curve is kept unchanged with increasing W up to 4 fW. The negative peak shift as well as its amplitude, together with the fact that these features are independent of W , definitely indicate that $\Delta\Sigma$ arises from the switch between the ground state (N_2) and the ionized state ($N_2 - 1$), as we have expected in Fig.1. On the other hand, the amplitude of $\Delta\Sigma$, (studied at the peak position marked by the arrow in Fig.3 (a)) linearly increases with increasing W only in a limited range of weak W but is saturated at higher levels as shown in the inset of Fig.3 (a). The saturation can be reasonably interpreted as a consequence that the rate of photon absorption at D2 exceeds the inverse lifetime, τ_l^{-1} , at $W \geq 1$ fW. The expected curve of saturation, $\Delta\Sigma \propto (1 + (\alpha/W))^{-1}$, well accounts for the

experimental data as shown by the solid line in the inset of Fig. 3(a), where $\alpha = h\nu/\eta\tau_l$ with the photon energy $h\nu$ and the quantum efficiency of photon absorption η . Noting $h\nu = 2$ meV and assuming $\eta = 10^{-2} \sim 10^{-3}$ [3], we roughly estimate $\tau_l = 0.1 \sim 1$ ms.

Additional evidence supporting our interpretation is presented in Fig. 3(b), where Σ and Σ_0 are shown against V_{G2} at fixed V_{G1} (-630mV) and V_{B12} (-530 mV). Here, Σ is taken under constant illumination at $W = 2$ fW. The values of Σ_0 reach the maximum at $V_{G2} = -565.2$ mV, where exact conductance resonance ($\mu_1 = \varepsilon_F$) takes place. In addition, as V_{G2} increases, Σ_0 shows an abrupt decrease and an abrupt increase, respectively, at the transition points $V_{G2}^t = -566.5$ mV and -564.4 mV, at which N_2 increases by one ($\Delta N_2 = +1$ at $\mu_2 = \varepsilon_F$). When SMMW is turned on, the conductance changes significantly on the positive sides of these V_{G2}^t transition points. The change is exactly the one expected from the removal of one electron from D2 ($\Delta N_2 = -1$), as may be understood from the conductance peak trace schematically illustrated on the upper part of Fig. 3 (b).

The V_{G2} -range where the photoresponse occurs is limited to a narrow interval on the positive side of V_{G2}^t . This is a general feature found at every transition point, and is interpreted by noting that the ionization energy of D2, $\Delta\varepsilon = \mu_2 - \varepsilon_F$, vanishes at $V_{G2} = V_{G2}^t$, but increases as V_{G2} goes away from V_{G2}^t towards the positive direction. This may lead to a rapid decrease both in τ_l and in the probability of photo-ionization, restricting the V_{G2} -range of the photoresponse as observed.

Excitation spectrum is studied by tuning the wavelength of the cyclotron emission line ($\Delta\nu \approx 1.5$ cm $^{-1}$) from the GaAs/AlGaAs emitter ($m^* = 0.067 m_0$) over a range 5 cm $^{-1} < \nu < 100$ cm $^{-1}$. The radiation intensity is chosen to be in a linear response regime ($W \approx 0.2$ fW). Figure 4 shows the B_e -dependence of $\Delta\Sigma$ at the peak position of the data in Fig. 3 (a), where B_e is converted to the frequency, $\nu = eB_e/2\pi m^*$. Distinct resonance is found at $\nu = 17$ cm $^{-1}$ ($h\nu = 2$ meV or $\lambda \approx 0.6$ mm) with a FWHM of $\Delta\nu_{\text{FWHM}} \approx 3.5$ cm $^{-1}$. We identify $\nu = 17$ cm $^{-1}$ as the Kohn-mode plasma resonance [7], because the value agrees with the calculation of the bare confinement potential for D2 as well as with the extrapolation of the (plasma-shifted) cyclotron resonance studied in our previous experiments on a similar QD (see Eq. (13) in [3]). We suppose that the initially excited collective motion of electrons is very rapidly transferred to a single electron excitation [8] (within a lifetime of $(2\pi\Delta\nu_{\text{FWHM}})^{-1} \approx 2.2$ ps), so that the excited electron with $E^* = h\nu = 2$ meV escapes from D2.

The sensitivity of detection is extremely high as suggested from the curve of $\Delta\Sigma$ versus W in the inset of Fig. 3 (a). Furthermore, it is noted to be close to the SPD level by the study of real-time trace of Σ . As shown in the inset of Fig. 4, photoresponse arises as irregular conductance spikes. Here, the data are taken with a time-constant of 3 ms at $W = 0.15$ fW in the same gate bias condition as that for the marked peak position in

Fig. 3 (a). The density of the conductance spikes increases with W . The positive spikes are ascribed to the switches, $N_2 \rightarrow N_2 - 1$, although individual events of photon absorption cannot be clearly discerned because τ_l (0.1 ~ 1 ms) is shorter than the time-constant of measurements. We find that the conductance spikes do not completely vanish in the dark condition, probably, because the sample is not perfectly shielded against the 4.2K-black-body radiation in the present work. Noting the dark switches, we roughly estimate NEP to be of the order of 10^{-17} W/ $\sqrt{\text{Hz}}$.

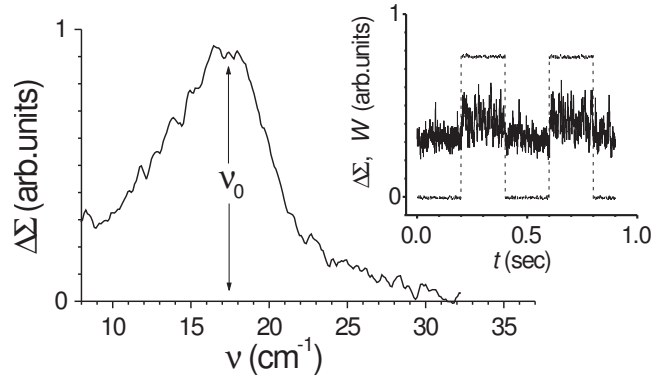


FIG. 4. The excitation spectrum of $\Delta\Sigma$, studied with $W = 0.15$ fW in the same gate bias condition as that of the V_{G1} -position marked by the arrow in Fig. 3 (a). The inset shows a real-time trace of the conductance at $W = 0.15$ fW taken in the same gate bias condition, where the square waveform indicates on-and-off of the SMMW.

In conclusion, we have demonstrated ultra-high sensitive detection of SMMW by using an SET consisting of parallel double QDs.

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